5P04

P-channel Enhancement Mode Power MosFET

V_{DSS}	-40 V
I_D	-5 A
$R_{DS(ON)}$	65mΩ

5P04

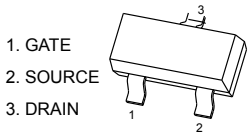
Features

- V_{DS}= -40V, I_D= -5A
  $R_{DS(ON)}$ < 85mΩ @ V_{GS} = -10V
  $R_{DS(ON)}$ < 115mΩ @ V_{GS} = -4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

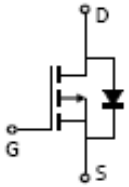
Applications

- PWM Applications
- Load Switch
- Power Management

SOT-23



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-40	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_A= 25℃	-5	A
		T_A= 100℃	-3.3	A
I_{DM}	Pulsed Drain Current note1		-20	A
P_D	Power Dissipation	T_A= 25℃	3.4	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		37	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25℃unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -40V, V_{GS}=0V	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-1.0	-1.6	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}= -10V, I_D= -3A	-	65	85	mΩ
		V_{GS}= -4.5V, I_D= -2A	-	90	115	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= -20V, V_{GS}=0V, f=1.0MHz	-	573	-	pF
C_{oss}	Output Capacitance		-	53	-	pF
C_{rss}	Reverse Transfer Capacitance		-	42	-	pF
Q_g	Total Gate Charge	V_{DS}= -20V, I_D= -3A, V_{GS}= -10V	-	7.1	-	nC
Q_{gs}	Gate-Source Charge		-	1.5	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	1.8	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}= -20V, I_D= -5A, V_{GS}= -10V, R_{GEN}=2.5Ω	-	6.5	-	ns
t_r	Turn-on Rise Time		-	14	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	34	-	ns
t_f	Turn-off Fall Time		-	18	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-20	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -5A	-	-0.8	-1.2	V
trr	Reverse Recovery Time	V_{GS}=0V, I_S= -5A, di/dt=100A/μs	-	23	-	ns
Qrr	Reverse Recovery Charge		-	25.2	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

RATING AND CHARACTERISTIC CURVES

Figure1: Output Characteristics

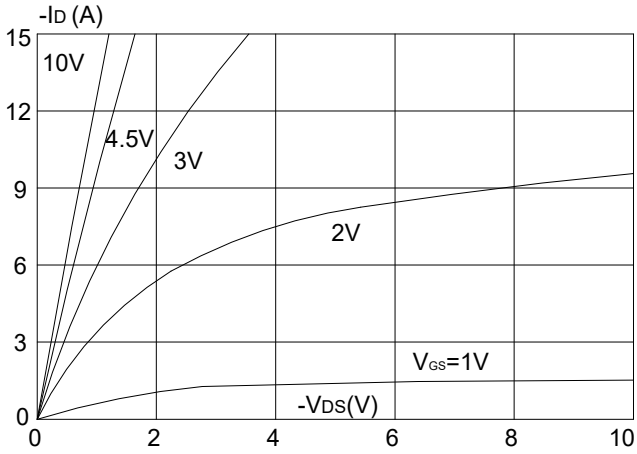


Figure 2: Typical Transfer Characteristics

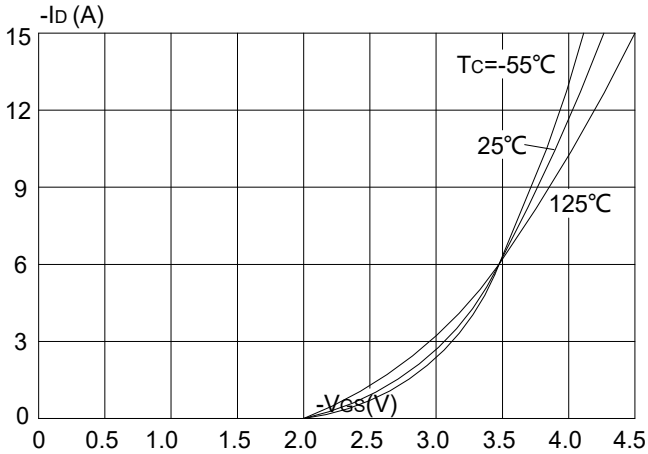


Figure 3: On-resistance vs. Drain Current

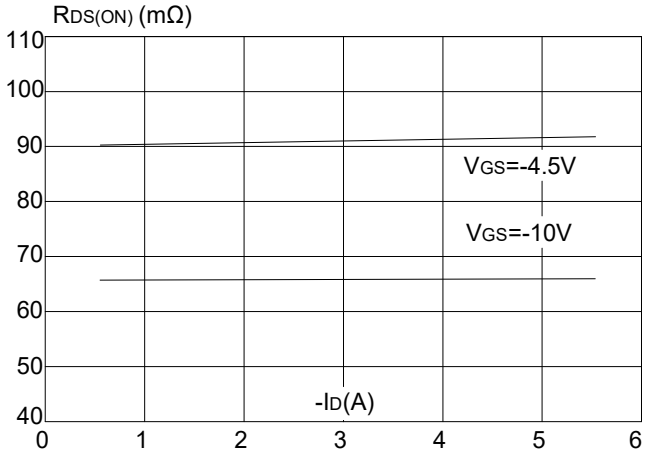


Figure 4: Body Diode Characteristics

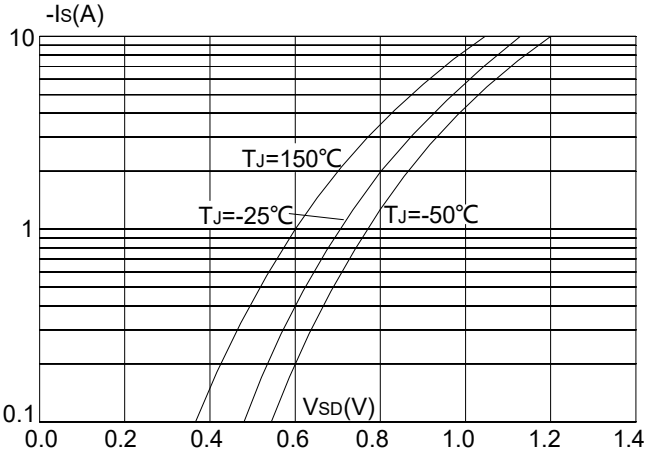


Figure 5: Gate Charge Characteristics

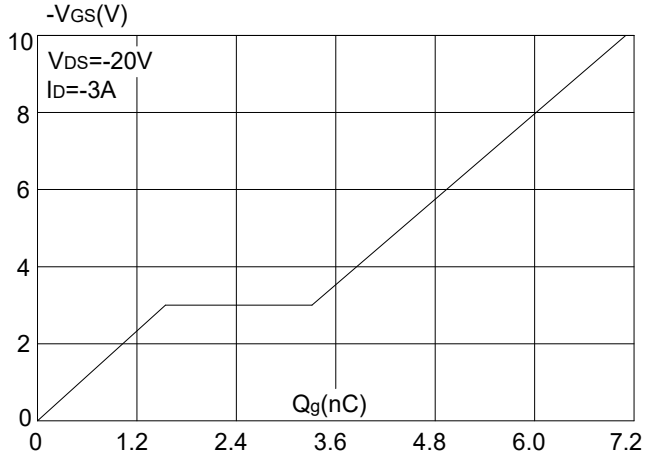
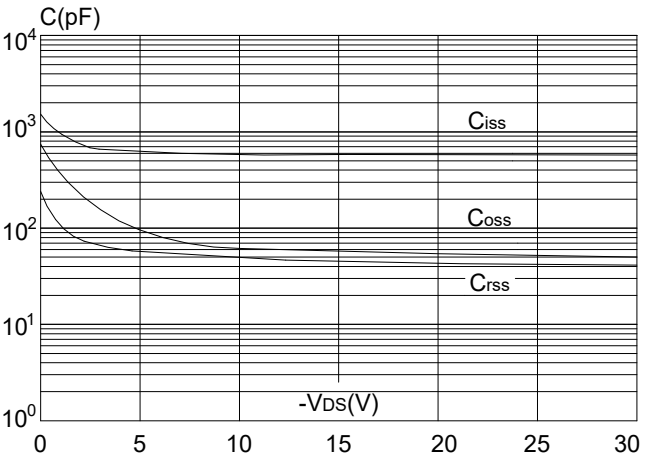


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

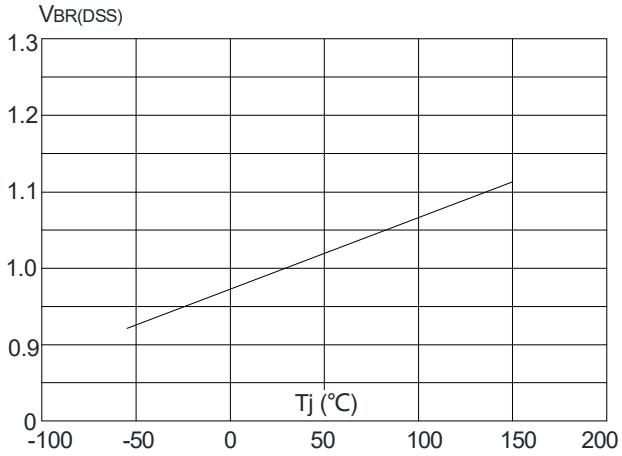


Figure 8: Normalized on Resistance vs. Junction Temperature

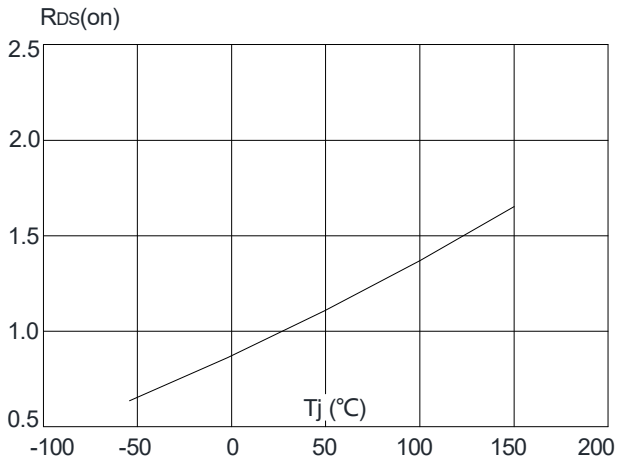


Figure 9: Maximum Safe Operating Area

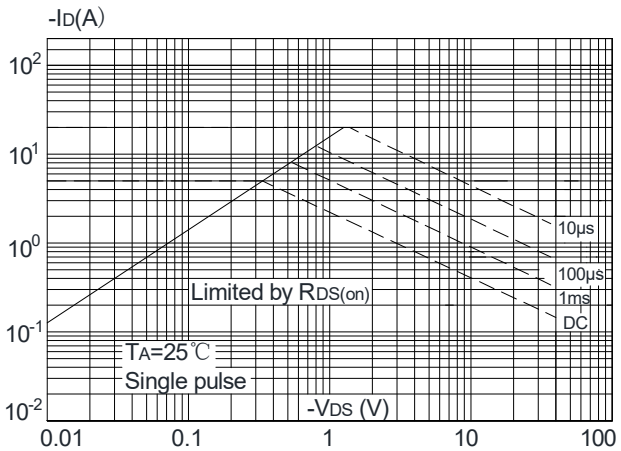


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

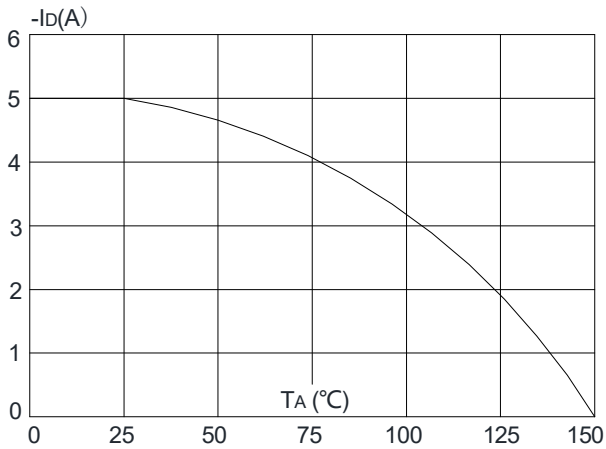
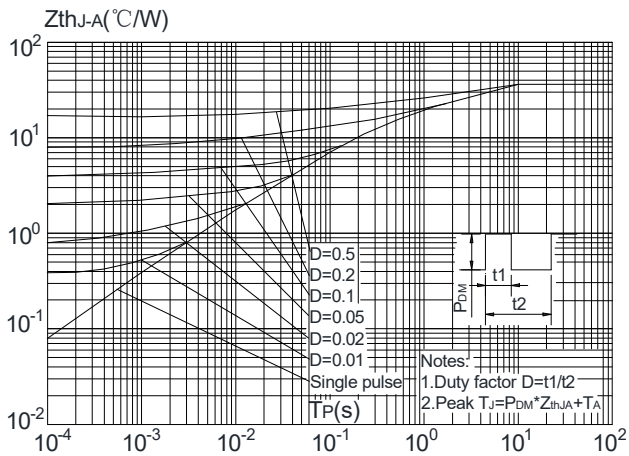


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit

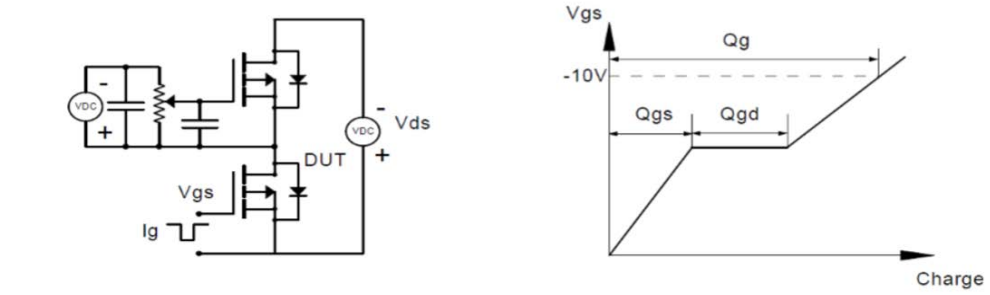


Figure 1: Gate Charge Test Circuit & Waveform

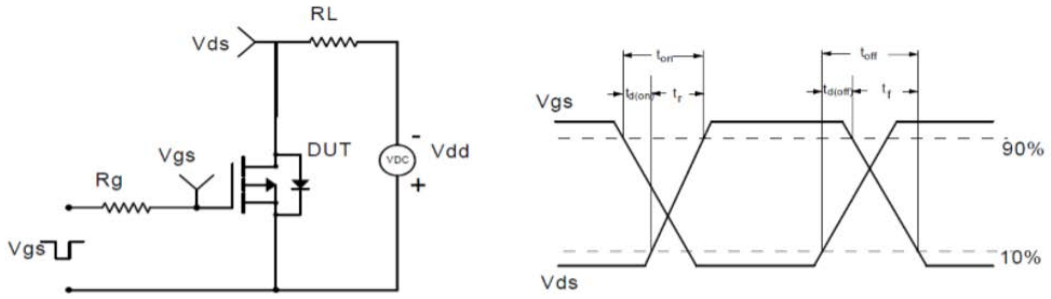


Figure 2: Resistive Switching Test Circuit & Waveform

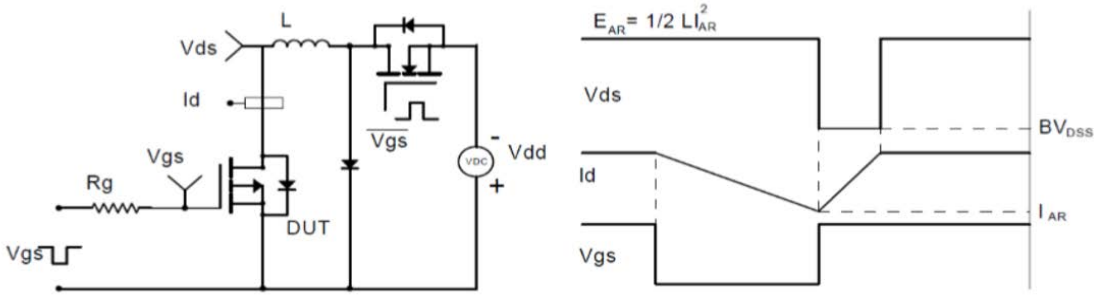


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

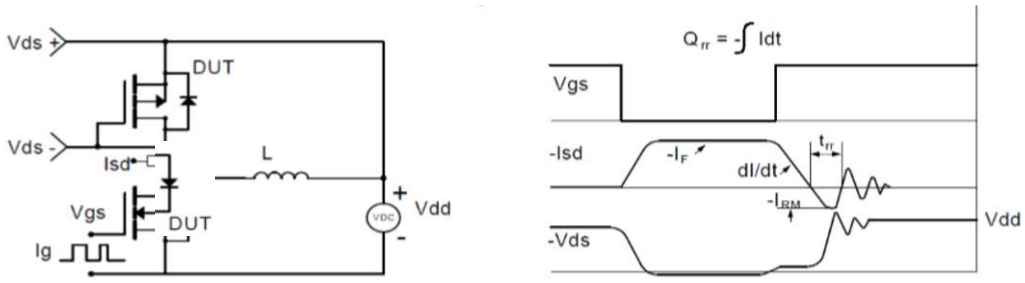
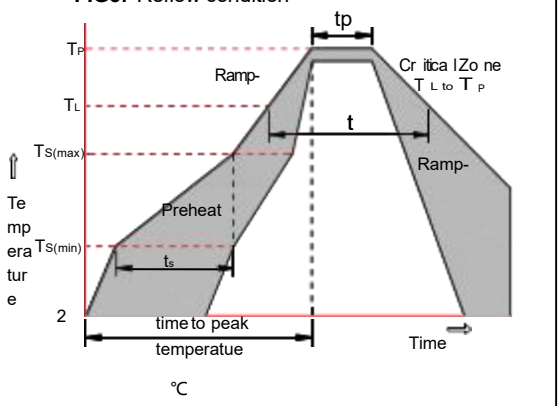


Figure 4: Diode Recovery Test Circuit & Waveform

Soldering parameters

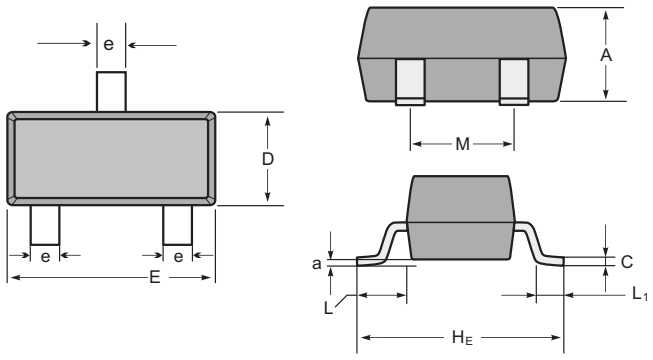
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

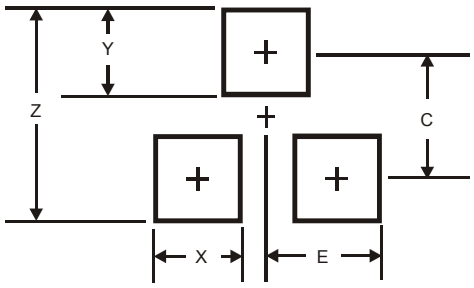
FIG5: Reflow condition



Package Dimensions & Suggested Pad Layout

SOT23





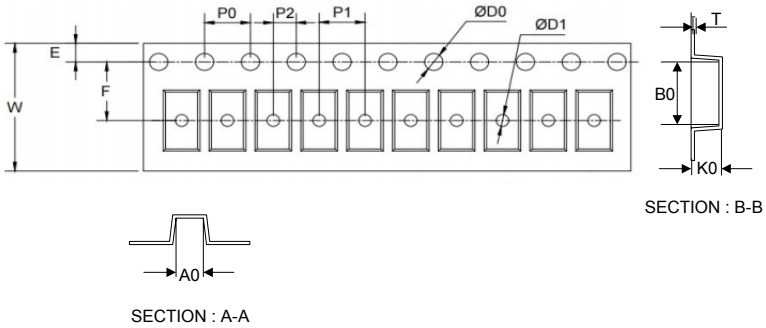
SOT-23 mechanical data

UNIT		A	C	D	E	H_E	e	M	L	L_1	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

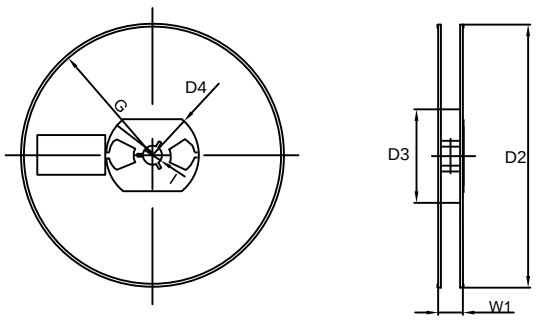
Tape & rell specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.10
P1	4.00±0.10
P2	2.00±0.10
D0	1.55±0.10
D1	1.05±0.10
E	1.55±0.10
F	3.60±0.10
W	8.00±0.10
A0	3.80±0.20
B0	3.25±0.20
K0	1.45±0.10
T	0.25±0.05

7” Reel



D2	178.0±3.0
D3	55Min.
D4	R24.0±3.0
G	R82.0±3.0
I	13.0±2.0
W1	11.0±3.0
Quantity: 3000PCS	